CGWT80N65F2SAD

V_{CE}	Ic (Tc=100℃)	$V_{CE(sat)}$
650V	80A	1.55V

TO-247



DESCRIPTION

The CGWT80N65F2SAD is used SZCJ 's second generation IGBT technology, has advanced Trench and FS(Field Stop) Structure，it's with high application frequent, low Collector-Emitter Saturation Voltage and switching loss, can easy to use in parallel.

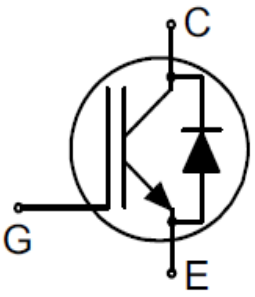
Features

- 650V breakdown Voltage
- Low Vce(sat) and positive temperature coefficient
- High speed switching，Low switching loss
- With fast and soft recovery freewheeling diode
- Good EMI behavior

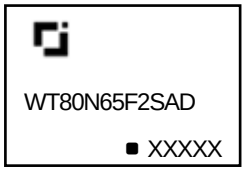
Application

- UPS & PFC applications
- Solar Inverter
- EV Charger
- Power Storage
- Welder

EQUIVALENT CIRCUIT



MARKING



WT80N65F2SAD = Device code

Solid dot = Green molding compound device, if none, the normal device

XXXX = Code

Order Code	Package	Marking	Parking
CGWT80N65F2SAD	TO-247	WT80N65F2SAD	Tube

感谢您的支持，如需要完整规格书，请联系：<igbt.list@szcjsemi.com >，谢谢!

Thank you for your support. If you need a complete datasheet, please contact:

<igbt.list@szcjsemi.com >. Thank you!